

NTD4854N-35G Information



For Reference Only

Part Number NTD4854N-35G Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 25V 15.7A IPAK

Package TO-251-3 Stub Leads, IPak

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









NTD4854N-35G Specifications

Manufacturer Part Number NTD4854N-35G Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Stub Leads, IPak Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 25V Current - Continuous Drain (Id) @ 25°C 15.7A (Ta), 128A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 49.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 4600pF @ 12V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.43W (Ta), 93.75W (Tc) Rds On (Max) @ Id, Vgs 3.6 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak		
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Package TO-251-3 Stub Leads, IPak Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 25V Current - Continuous Drain (Id) @ 25°C 15.7A (Ta), 128A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 49.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 460pF @ 12V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.43W (Ta), 93.75W (Tc) Rds On (Max) @ Id, Vgs 3.6 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Manufacturer	ON Semiconductor
Package TO-251-3 Stub Leads, IPak Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 25V Current - Continuous Drain (Id) @ 25°C 15.7A (Ta), 128A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 49.2n C @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 4600p F @ 12V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.43W (Ta), 93.75W (Tc) Rds On (Max) @ Id, Vgs 3.6 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Category	Discrete Semiconductor Products
Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 25V Current - Continuous Drain (Id) @ 25°C 15.7A (Ta), 128A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 49.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 4600pF @ 12V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.43W (Ta), 93.75W (Tc) Rds On (Max) @ Id, Vgs 3.6 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.6 mOhm @ 30A, 10V Operating Temperature Mounting Type Supplier Device Package Package / Case N-Channel AUSFET (Metal Oxide) 25V 25V 25V 25V 25V 4.5V 4.5V, 10V 4.5	Package	TO-251-3 Stub Leads, IPak
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)25VCurrent - Continuous Drain (Id) @ 25°C15.7A (Ta), 128A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs49.2nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds4600pF @ 12VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.43W (Ta), 93.75W (Tc)Rds On (Max) @ Id, Vgs3.6 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Stub Leads, IPak	Series	-
Drain to Source Voltage (Vdss)25VCurrent - Continuous Drain (Id) @ 25°C15.7A (Ta), 128A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs49.2nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds4600pF @ 12VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.43W (Ta), 93.75W (Tc)Rds On (Max) @ Id, Vgs3.6 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Stub Leads, IPak	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.6 mOhm @ 30A, 10V Operating Temperature Supplier Device Package Package / Case 15.7A (Ta), 128A (Tc) 15.7A (Ta), 128A	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs49.2nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds4600pF @ 12VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.43W (Ta), 93.75W (Tc)Rds On (Max) @ Id, Vgs3.6 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Stub Leads, IPak	Drain to Source Voltage (Vdss)	25V
Vgs(th) (Max) @ Id 2.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 49.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 4600pF @ 12V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.43W (Ta), 93.75W (Tc) Rds On (Max) @ Id, Vgs 3.6 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Current - Continuous Drain (Id) @ 25°C	15.7A (Ta), 128A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 4600pF @ 12V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.6 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.6 mOhm @ 30A, 10V Operating Temperature Coperating Type Through Hole Supplier Device Package Feature 1-20V 1.43W (Ta), 93.75W (Tc) 3.6 mOhm @ 30A, 10V Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Vgs(th) (Max) @ Id	2.5V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.43W (Ta), 93.75W (Tc)Rds On (Max) @ Id, Vgs3.6 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Stub Leads, IPak	Gate Charge (Qg) (Max) @ Vgs	49.2nC @ 4.5V
FET Feature - 1.43W (Ta), 93.75W (Tc) Rds On (Max) @ Id, Vgs 3.6 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Input Capacitance (Ciss) (Max) @ Vds	4600pF @ 12V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.6 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs3.6 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Stub Leads, IPak	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Power Dissipation (Max)	1.43W (Ta), 93.75W (Tc)
Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Rds On (Max) @ Id, Vgs	3.6 mOhm @ 30A, 10V
Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-251-3 Stub Leads, IPak	Mounting Type	Through Hole
	Supplier Device Package	I-Pak
Report errors?	Package / Case	TO-251-3 Stub Leads, IPak
		Report errors?

NTD4854N-35G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NTD4854N-35G Payment Methods



















NTD4854N-35G Shipping Methods













If you have any question about NTD4854N-35G, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com